



PHPT60603PY

60 V, 3 A PNP high power bipolar transistor

13 January 2014

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60603NY.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

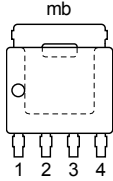
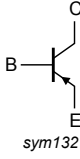
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-60	V
I_C	collector current		-	-	-3	A
I_{CM}	peak collector current	$t_p \leq 1$ ms; pulsed	-	-	-8	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -3$ A; $I_B = -300$ mA; pulsed; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_{amb} = 25$ °C	-	80	120	m Ω



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p>LFPAK56; Power-SO8 (SOT669)</p>	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT60603PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60603PY	0603PAB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

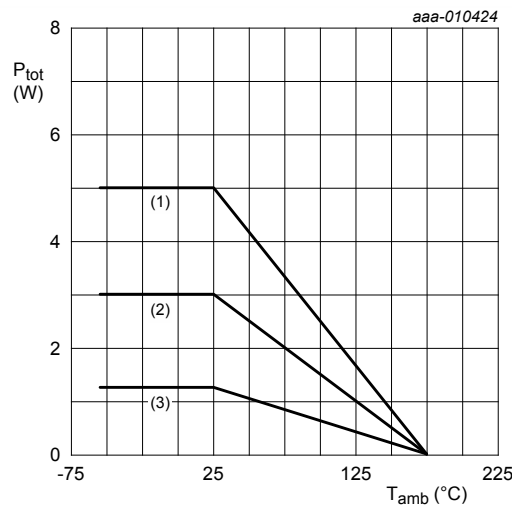
Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-60	V
V_{CEO}	collector-emitter voltage	open base		-	-60	V
V_{EBO}	emitter-base voltage	open collector		-	-8	V
I_C	collector current			-	-3	A
I_{CM}	peak collector current	$t_p \leq 1$ ms; pulsed		-	-8	A
I_B	base current			-	-0.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T_j	junction temperature			-	175	°C
T_{amb}	ambient temperature			-55	175	°C
T_{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[4] Power dissipation from junction to mounting base.



(1) Ceramic PCB, Al₂O₃, standard footprint

(2) FR4 PCB, mounting pad for collector 6 cm²

(3) FR4 PCB, standard footprint

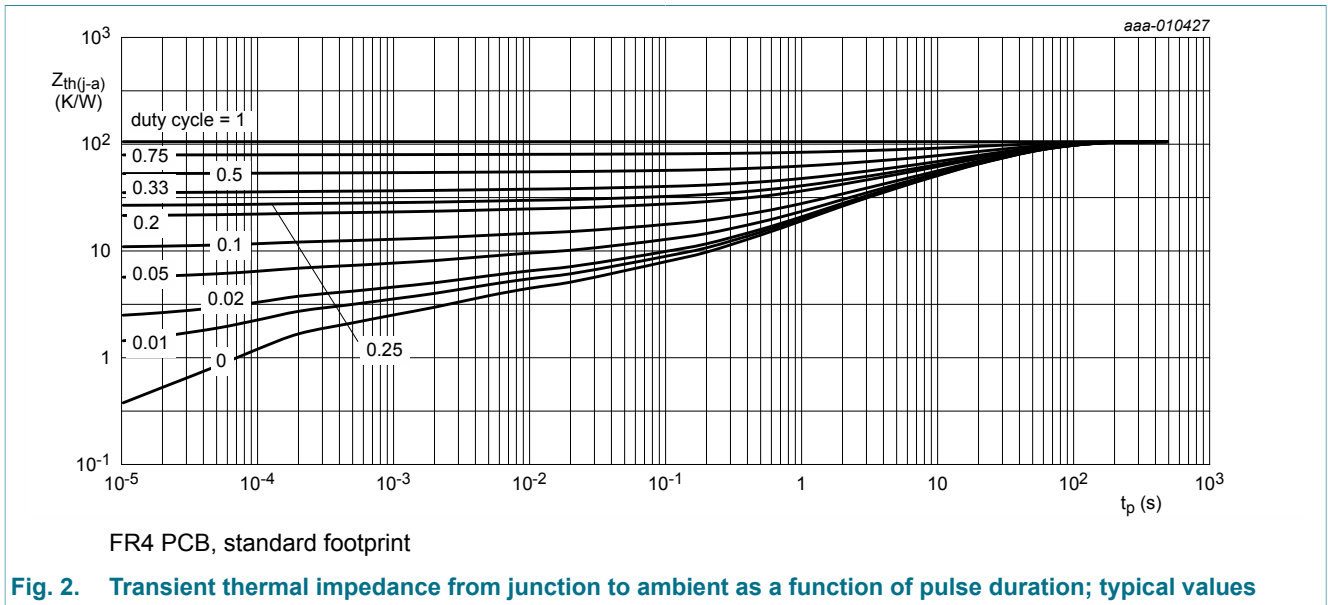
Fig. 1. Power derating curves

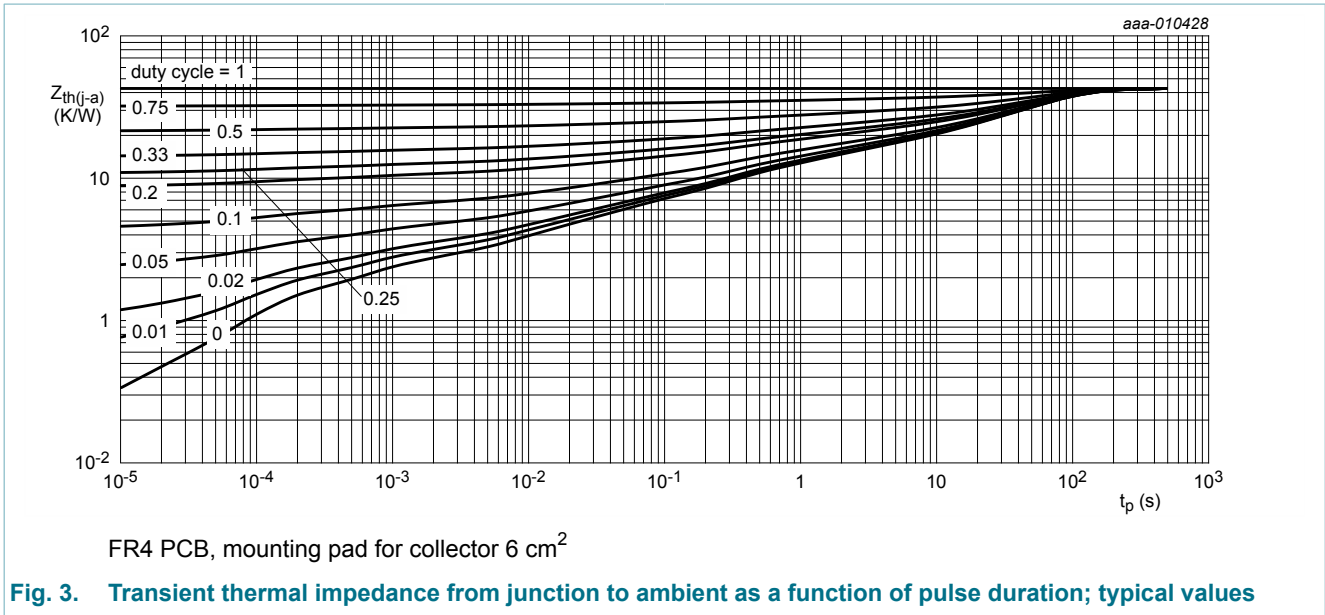
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	50	K/W
			[3]	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



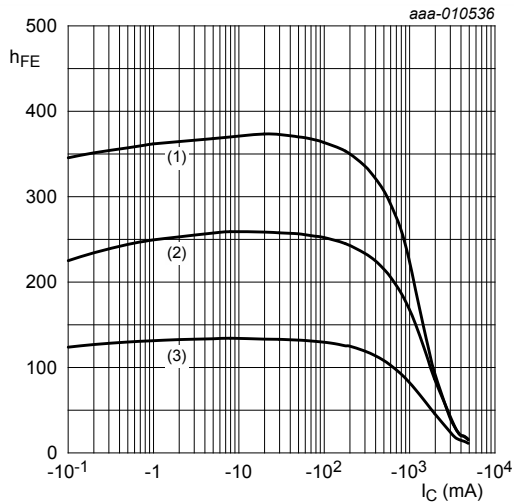


10. Characteristics

Table 7. Characteristics

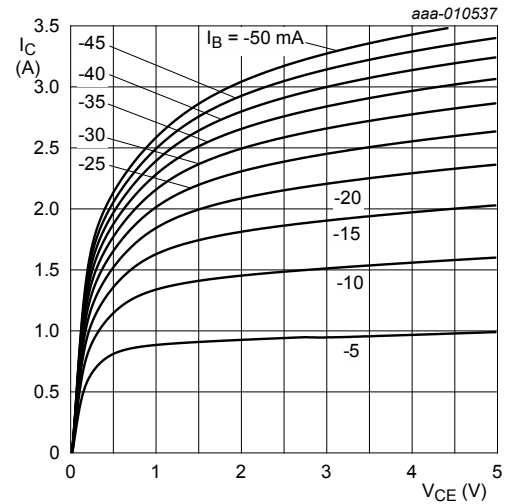
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
		V _{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -8 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -500 mA; T _{amb} = 25 °C	150	250	-	
		V _{CE} = -2 V; I _C = -1 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	150	225	-	
		V _{CE} = -2 V; I _C = -2 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	80	130	-	
		V _{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	35	75	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -1 A; I _B = -50 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-100	-225	mV
		I _C = -3 A; I _B = -300 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	-	-240	-360	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = -1 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	100	225	mΩ
		I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	80	120	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-0.89	-1	V
		I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-1.02	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -0.1 A; T _{amb} = 25 °C	-	-0.83	-0.9	V
t _d	delay time	V _{CC} = -12.5 V; I _C = -1 A; I _{Bon} = -50 mA; I _{Boff} = 50 mA; T _{amb} = 25 °C	-	15	-	ns
t _r	rise time		-	85	-	ns
t _{on}	turn-on time		-	100	-	ns
t _s	storage time		-	350	-	ns
t _f	fall time		-	110	-	ns
t _{off}	turn-off time		-	460	-	ns
f _T	transition frequency		V _{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	-	110	-

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	60	-	pF



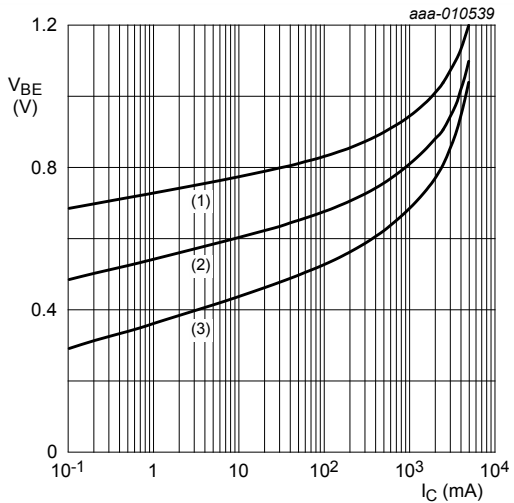
$V_{CE} = -1\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 4. DC current gain as a function of collector current; typical values



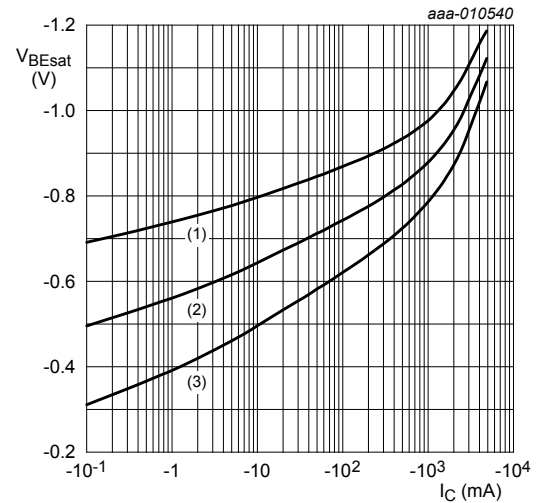
$T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 5. Collector current as a function of collector-emitter voltage; typical values



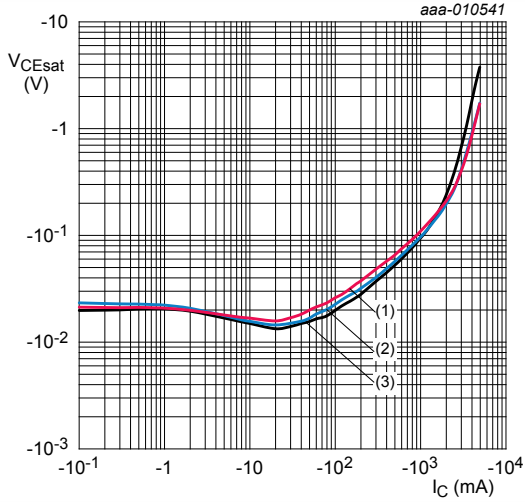
$V_{CE} = -2\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



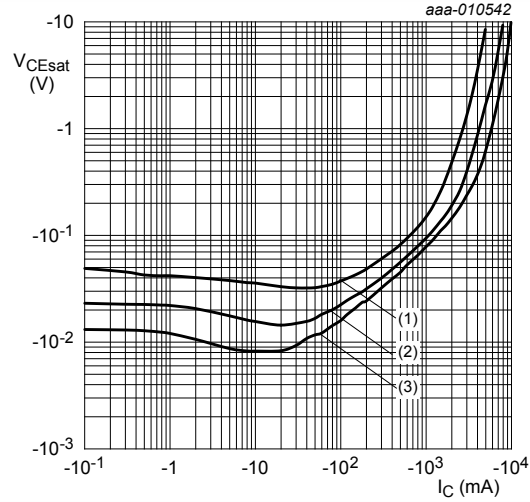
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



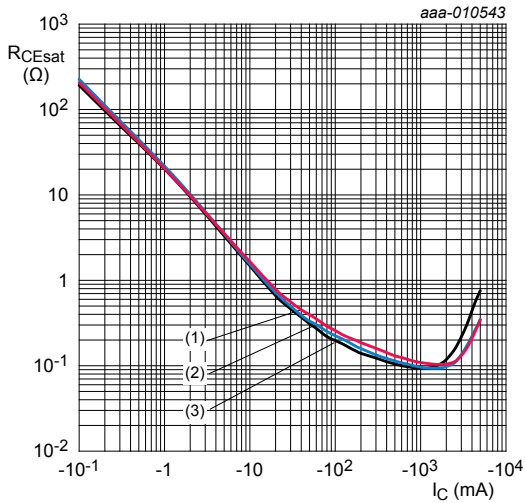
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



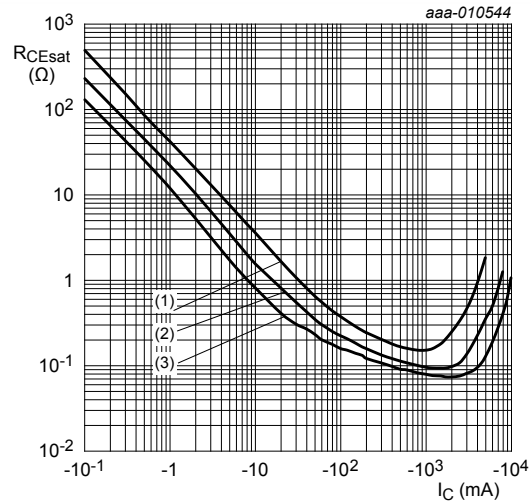
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 50$
 (2) $I_C/I_B = 20$
 (3) $I_C/I_B = 10$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 50$
 (2) $I_C/I_B = 20$
 (3) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

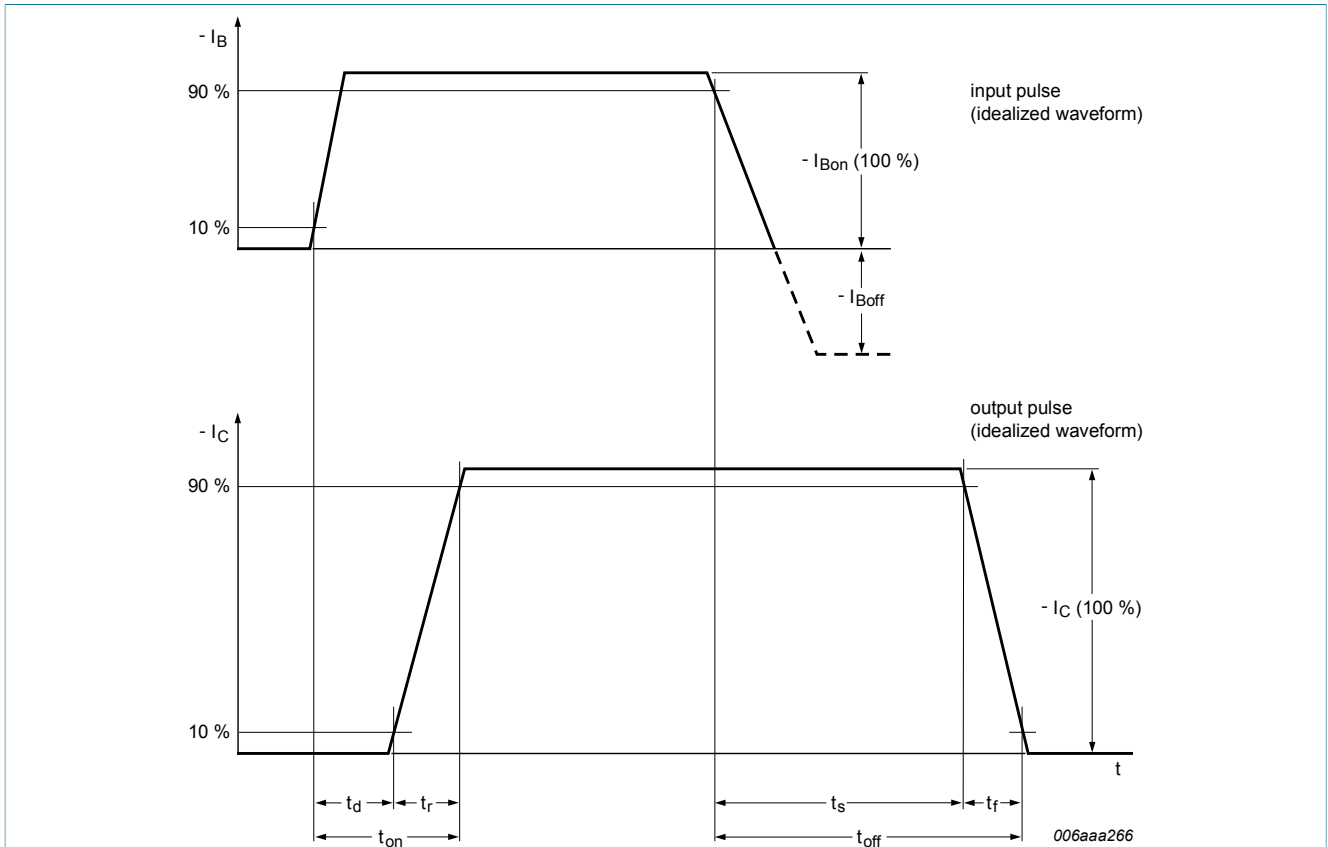


Fig. 12. BISS transistor switching time definition

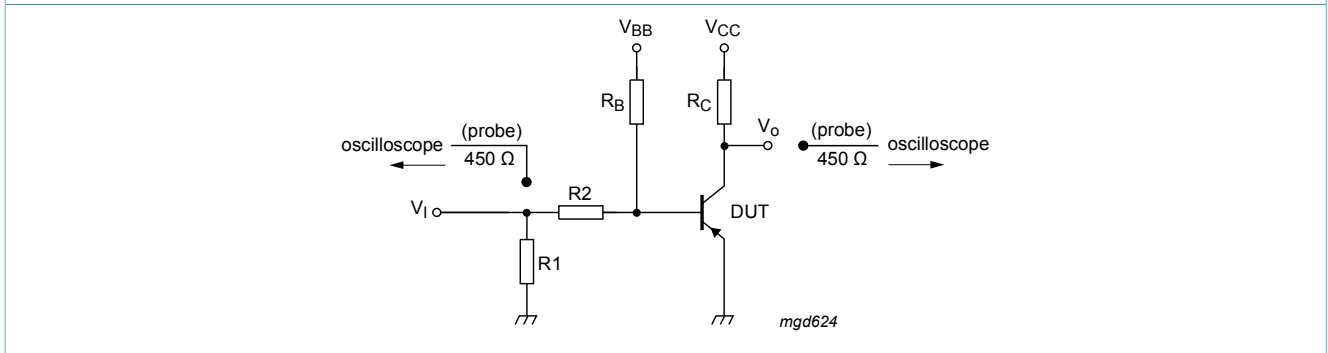


Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads SOT669



Dimensions (mm are the original dimensions)

Unit ⁽¹⁾	A	A ₁	A ₂	A ₃	b	b ₂	b ₃	b ₄	c	c ₂	D ⁽¹⁾	D ₁ ⁽¹⁾	E ⁽¹⁾	E ₁ ⁽¹⁾	e	H	L	L ₁	L ₂	w	y
max	1.20	0.15	1.10		0.50	4.41	2.2	0.9	0.25	0.30	4.10	4.20	5.0	3.3		6.2	0.85	1.3	1.3		
nom				0.25											1.27					0.25	0.1
min	1.01	0.00	0.95		0.35	3.62	2.0	0.7	0.19	0.24	3.80		4.8	3.1		5.8	0.40	0.8	0.8		

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

sot669_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT669		MO-235				-11-03-25- 13-02-27

Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

13. Soldering

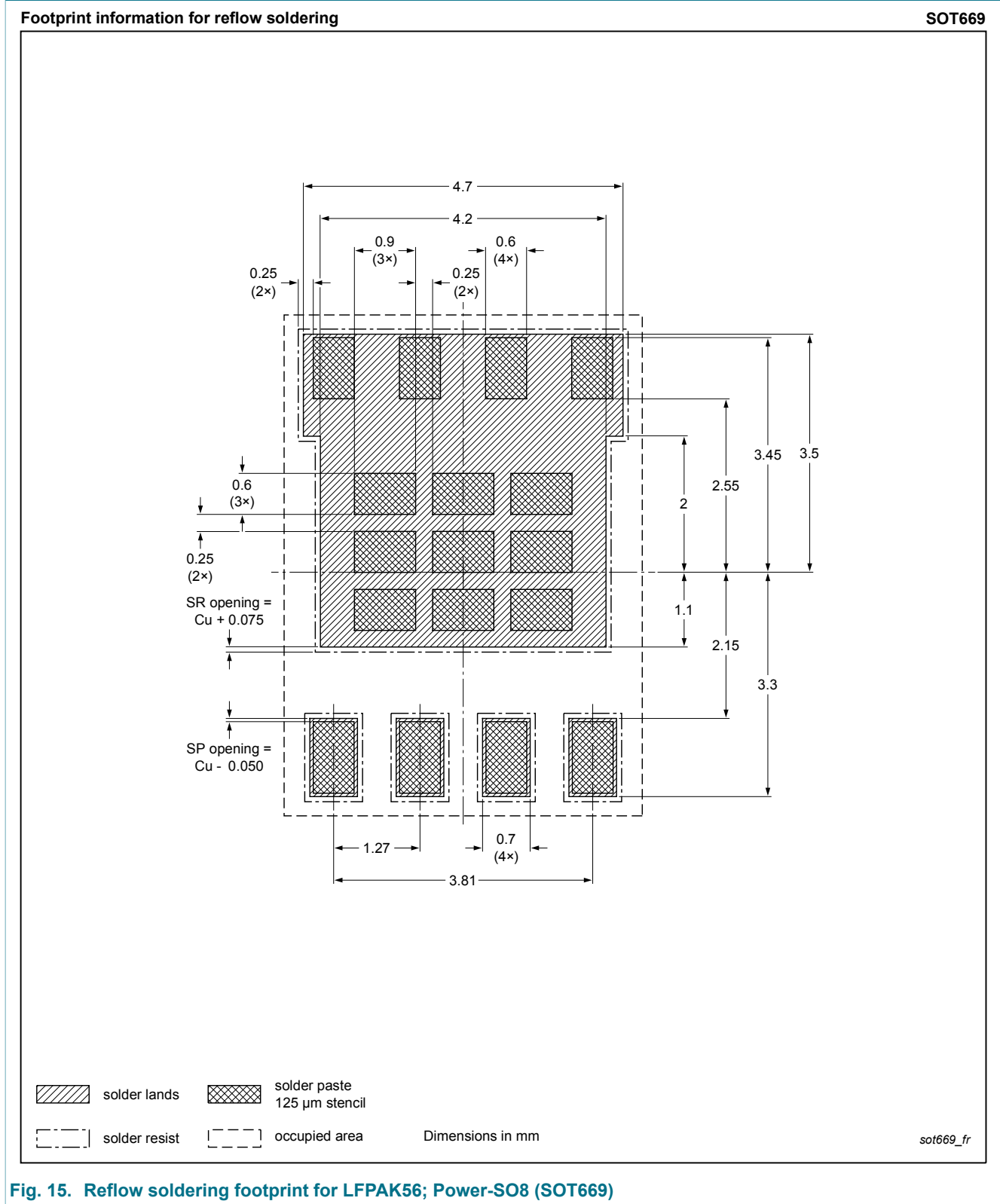


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60603PY v.1	20140113	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
11.1	Quality information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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Date of release: 13 January 2014
